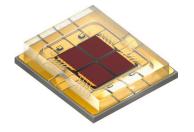
OSRAM LE R S2WP **Datasheet**



OSRAM OSTAR® Stage

LERS2WP

Outstanding brightness and luminance due to surface emission and low Rth





Applications

- Entertainment

- Factory Automation

Features

- Package: compact lightsource in multi chip SMT technology with glass window on top
- Chip technology: Thinfilm
- Typ. Radiation: 120° (Lambertian emitter)
- Color: λ_{dom} = 625 nm (• red)
- Corrosion Robustness Class: 3B
- ESD: 2 kV acc. to ANSI/ESDA/JEDEC JS-001 (HBM, Class 2)

LE R S2WP DATASHEET



Ord	lering	Inform	ation
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Ordering Code Type Luminous Flux 1) $I_{E} = 1400 \text{ mA}$

 $\boldsymbol{\varphi}_{\!_{\boldsymbol{V}}}$

500 ... 1000 lm LE R S2WP-6P7Q-25-0 Q65113A8258 LE R S2WP **DATASHEET**



Maximum Ratings			
Parameter	Symbol		Values
Operating Temperature	T _{op}	min.	-40 °C
	σp	max.	85 °C
Storage Temperature	T _{stg}	min.	-40 °C
	3.9	max.	85 °C
Junction Temperature	T_{j}	max.	125 °C
Forward Current	I _E	min.	100 mA
T _S = 25 °C; per chip	•	max.	5000 mA
ESD withstand voltage acc. to ANSI/ESDA/JEDEC JS-001 (HBM, Class 2)	V_{ESD}		2 kV
Reverse current 2)	I _R	max.	200 mA



Characteristics

 I_F = 1400 mA; T_S = 25 °C; per chip

Parameter	Symbol		Values
Peak Wavelength	λ_{peak}	typ.	633 nm
Dominant Wavelength 3)	$\lambda_{\sf dom}$	min.	615 nm
	40	typ.	625 nm
		max.	629 nm
Viewing angle at 50% I _V	2φ	typ.	120 °
Radiating surface	A_{color}	typ.	2.5 x 3.2 mm ²
Partial Flux acc. CIE 127:2007 4)	$\Phi_{\text{E/V, 120}^\circ}$	typ.	0.69
$I_F = 1400 \text{ mA}$	27, 120		
Forward Voltage 5)	V _F	min.	1.90 V
$I_{\rm F} = 1400 \text{ mA}$		typ.	2.35 V
		max.	2.80 V
Reverse voltage (ESD device)	V_{RESD}	min.	45 V
Reverse voltage 2)	$V_{_{\mathrm{R}}}$	max.	1.2 V
$I_R = 20 \text{ mA}$	TX		
Real thermal resistance junction/solderpoint ⁶⁾	$R_{ ext{thJS real}}$	typ.	0.70 K / W
		max.	0.80 K / W
Electrical thermal resistance junction/solderpoint ⁶⁾	R _{thJS elec.}	typ.	0.50 K / W
with efficiency η_e = 29 %		max.	0.57 K / W



Brightness Groups

Group	Luminous Flux 1) I _E = 1400 mA	Luminous Flux 1) I _E = 1400 mA	
	min.	max.	
	Φ_{V}	Φ_{V}	
6P	500 lm	560 lm	
7P	560 lm	630 lm	
8P	630 lm	710 lm	
5Q	710 lm	800 lm	
6Q	800 lm	900 lm	
7Q	900 lm	1000 lm	

Wavelength Groups

Group	Dominant Wavelength 3)	Dominant Wavelength 3)
	min.	max.
	$\lambda_{\sf dom}$	$\lambda_{\sf dom}$
2	615 nm	619 nm
3	618 nm	622 nm
4	621 nm	625 nm
5	624 nm	629 nm

Group Name on Label

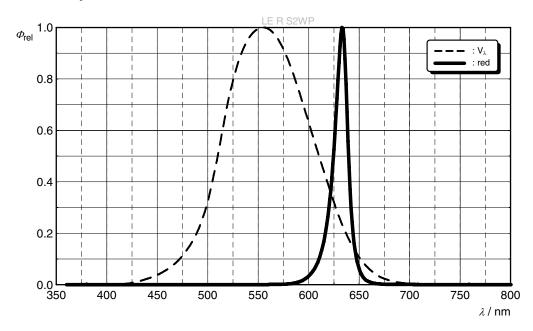
Example: 5Q-2

Brightness	Wavelength
5Q	2



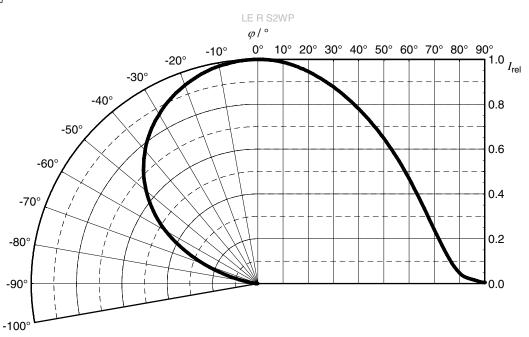
Relative Spectral Emission 4)

$$\Phi_{rel}$$
 = f (λ); I_F = 1400 mA; T_J = 25 °C



Radiation Characteristics 4)

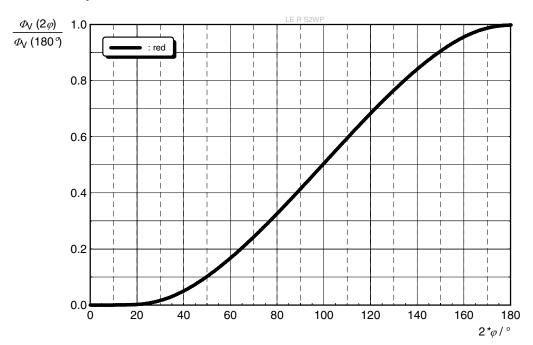
$$I_{rel} = f(\phi); T_J = 25 \, ^{\circ}C$$





Relative Partial Flux 4)

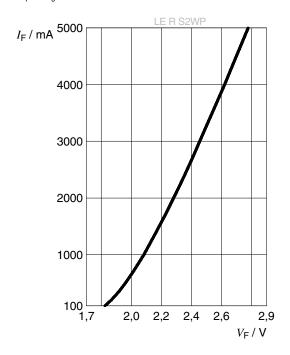
 $\Phi_{_{\text{V/E}}}(2\phi)/\Phi_{_{\text{V/E}}}(180^\circ) = f(\phi); \, T_{_J} = 25 \,\, ^\circ C$





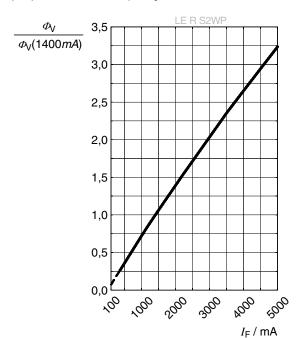
Forward current 4)

 $I_F = f(V_F); T_J = 25 \,^{\circ}C; per Chip$



Relative Luminous Flux 4), 7)

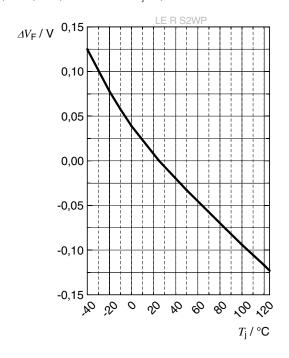
 $\Phi_{V}/\Phi_{V}(1400 \text{ mA}) = f(I_{F}); T_{J} = 25 \text{ °C}; per Chip}$



OSRAM

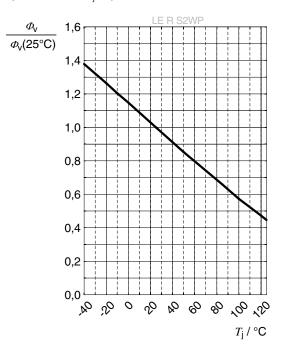
Forward Voltage 4)

 $\Delta V_F = V_F - V_F (25 \text{ °C}) = f(T_j); I_F = 1400 \text{ mA; per Chip}$



Relative Luminous Flux 4)

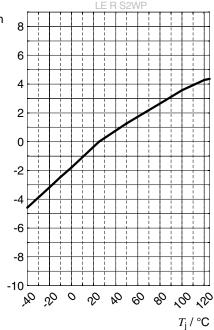
 $\Phi_{V}/\Phi_{V}(25 \text{ °C}) = f(T_{i}); I_{E} = 1400 \text{ mA}; per Chip}$



Dominant Wavelength 4)

 $\Delta\lambda_{\text{dom}} = \lambda_{\text{dom}} - \lambda_{\text{dom}} (25 \ ^{\circ}\text{C}) = f(T_{j}); \ I_{F} = 1400 \ \text{mA}; \ \text{per Chip}$

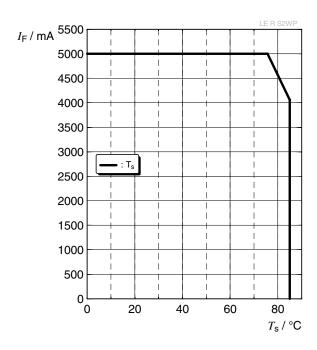
 $\Delta\lambda$ dom / nm





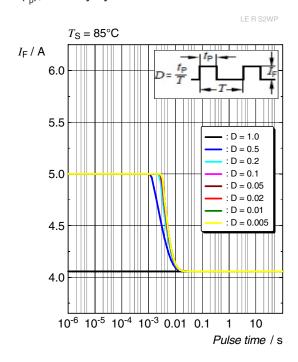
Max. Permissible Forward Current 6)

 $I_{\scriptscriptstyle F} = f(T)$



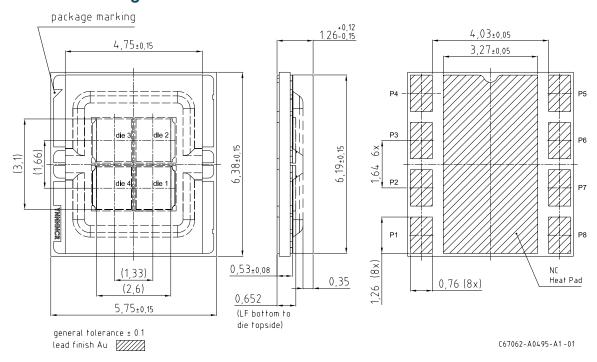
Permissible Pulse Handling Capability

 $I_F = f(t_p)$; D: Duty cycle





Dimensional Drawing 8)



Further Information:

Approximate Weight: 127.0 mg

Corrosion test: Class: 3B

Test condition: 40°C / 90 % RH / 15 ppm H₂S / 14 days (stricter than IEC

60068-2-43)

ESD advice: The device is protected by ESD device which is connected in parallel to the

Chip.

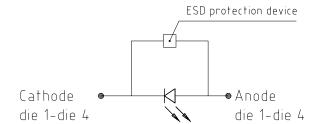


Electrical Internal Circuit

Pinning:

P1 Cathode die 1 P5 Cathode die 3 P2 Anode die 1 P6 Anode die 3

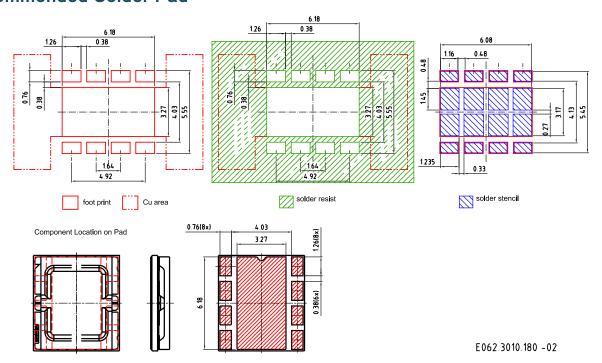
P3 Anode die 2 P7 Anode die 4 P4 Cathode die 2 P8 Cathode die 4



Colors:

die 1: red die 2: red die 3: red die 4: red

Recommended Solder Pad 8)

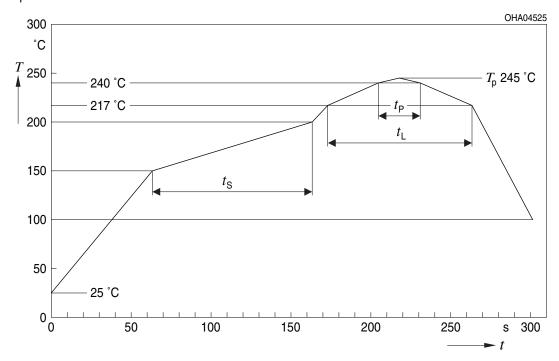


For superior solder joint connectivity results we recommend soldering under standard nitrogen atmosphere. Package not suitable for any kind of wet cleaning or ultrasonic cleaning.



Reflow Soldering Profile

Product complies to MSL Level 2 acc. to JEDEC J-STD-020E



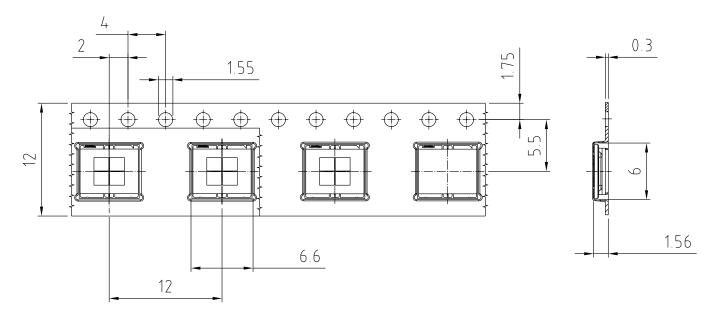
Profile Feature	Symbol	Pb	-Free (SnAgCu) Ass	sembly	Unit
		Minimum	Recommendation	Maximum	
Ramp-up rate to preheat*)	'		2	3	K/s
25 °C to 150 °C					
Time t _s	t _s	60	100	120	S
T_{Smin} to T_{Smax}					
Ramp-up rate to peak*)			2	3	K/s
T_{Smax} to T_{P}					
Liquidus temperature	T_{L}		217		°C
Time above liquidus temperature	$t_{\scriptscriptstyle \perp}$		80	100	S
Peak temperature	T _P		245	260	°C
Time within 5 °C of the specified peak	t _P	10	20	30	S
temperature T _P - 5 K					
Ramp-down rate* T _P to 100 °C			3	6	K/s
Time 25 °C to T _P				480	S
20 0 to 1 _P					

All temperatures refer to the center of the package, measured on the top of the component

^{*} slope calculation DT/Dt: Dt max. 5 s; fulfillment for the whole T-range



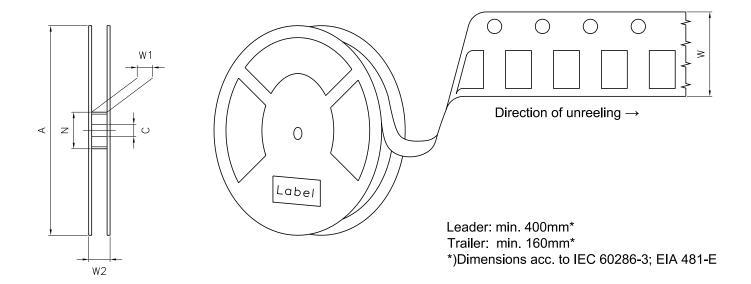
Taping 8)



C67062-A0495-B8 -01



Tape and Reel 9)

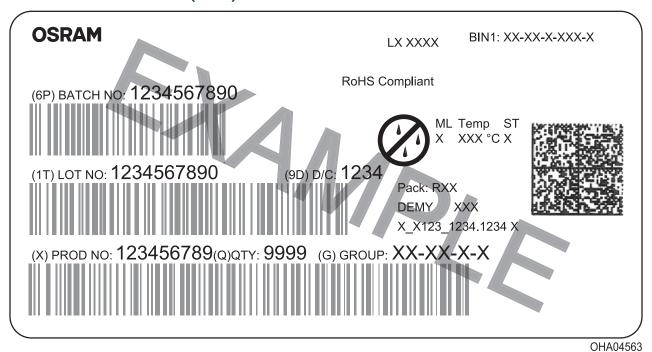


Reel Dimensions

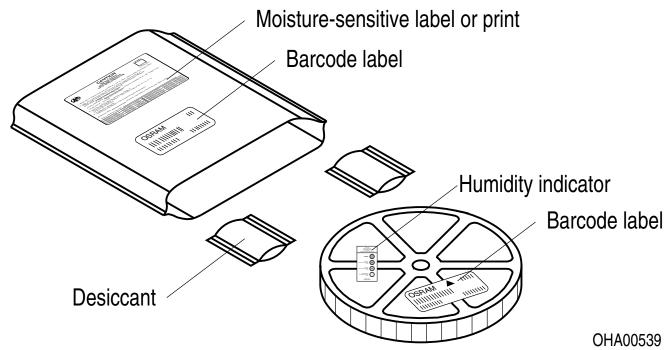
Α	W	N_{\min}	W_1	$W_{2 \text{max}}$	Pieces per PU
180 mm	12 + 0.3 / - 0.1 mm	60 mm	12.4 + 2 mm	18.4 mm	500



Barcode-Product-Label (BPL)



Dry Packing Process and Materials 8)



Moisture-sensitive product is packed in a dry bag containing desiccant and a humidity card according JEDEC-STD-033.

LE R S2WP **DATASHEET**



Notes

The evaluation of eye safety occurs according to the standard IEC 62471:2006 (photo biological safety of lamps and lamp systems). Within the risk grouping system of this IEC standard, the device specified in this data sheet fall into the class exempt group (exposure time 10000 s). Under real circumstances (for exposure time, conditions of the eye pupils, observation distance), it is assumed that no endangerment to the eye exists from these devices. As a matter of principle, however, it should be mentioned that intense light sources have a high secondary exposure potential due to their blinding effect. When looking at bright light sources (e.g. headlights), temporary reduction in visual acuity and afterimages can occur, leading to irritation, annoyance, visual impairment, and even accidents, depending on the situation.

Subcomponents of this device contain, in addition to other substances, metal filled materials including silver. Metal filled materials can be affected by environments that contain traces of aggressive substances. Therefore, we recommend that customers minimize device exposure to aggressive substances during storage, production, and use. Devices that showed visible discoloration when tested using the described tests above did show no performance deviations within failure limits during the stated test duration. Respective failure limits are described in the IEC60810.

For further application related information please visit https://ams-osram.com/support/application-notes



Disclaimer

Attention please!

The information describes the type of component and shall not be considered as assured characteristics. Terms of delivery and rights to change design reserved. Due to technical requirements components may contain dangerous substances.

For information on the types in question please contact our Sales Organization.

If printed or downloaded, please find the latest version on our website.

Packing

Please use the recycling operators known to you. We can also help you – get in touch with your nearest sales office. By agreement we will take packing material back, if it is sorted. You must bear the costs of transport. For packing material that is returned to us unsorted or which we are not obliged to accept, we shall have to invoice you for any costs incurred.

Product and functional safety devices/applications or medical devices/applications

Our components are not developed, constructed or tested for the application as safety relevant component or for the application in medical devices.

Our products are not qualified at module and system level for such application.

In case buyer – or customer supplied by buyer – considers using our components in product safety devices/ applications or medical devices/applications, buyer and/or customer has to inform our local sales partner immediately and we and buyer and /or customer will analyze and coordinate the customer-specific request between us and buyer and/or customer.



Glossary

- Brightness: Brightness values are measured during a current pulse of typically 25 ms, with an internal reproducibility of ±8 % and an expanded uncertainty of ±11 % (acc. to GUM with a coverage factor of k = 3).
- Reverse Operation: This product is intended to be operated applying a forward current within the specified range. Applying any continuous reverse bias or forward bias below the voltage range of light emission shall be avoided because it may cause migration which can change the electro-optical characteristics or damage the LED.
- Wavelength: The wavelength is measured at a current pulse of typically 25 ms, with an internal reproducibility of ±0.5 nm and an expanded uncertainty of ±1 nm (acc. to GUM with a coverage factor of k =
- Typical Values: Due to the special conditions of the manufacturing processes of semiconductor devices, the typical data or calculated correlations of technical parameters can only reflect statistical figures. These do not necessarily correspond to the actual parameters of each single product, which could differ from the typical data and calculated correlations or the typical characteristic line. If requested, e.g. because of technical improvements, these typ. data will be changed without any further notice.
- Forward Voltage: The forward voltage is measured during a current pulse of typically 8 ms, with an internal reproducibility of ±0.05 V and an expanded uncertainty of ±0.1 V (acc. to GUM with a coverage factor of k = 3).
- 6) Thermal Resistance: Rth max is based on statistic values (6 σ) used for Derating.
- 7) Characteristic curve: In the range where the line of the graph is broken, you must expect higher differences between single devices within one packing unit.
- Tolerance of Measure: Unless otherwise noted in drawing, tolerances are specified with ±0.1 and dimensions are specified in mm.
- 9) Tape and Reel: All dimensions and tolerances are specified acc. IEC 60286-3 and specified in mm.

LE R S2WP DATASHEET



Revision History

Version	Date	Change
1.0	2025-02-19	New Layout



EU RoHS and China RoHS compliant product 此产品符合欧盟 RoHS 指令的要求; 按照中国的相关法规和标准, 不含有毒有害物质或元素。

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